

DETECTORS

PIPS® Detectors

Passivated Implanted Planar Silicon Detectors



FEATURES

- · Ion-implanted contacts
- · SiO₂ passivated
- · Low leakage current
- · Low noise
- · Thin window
- Cleanable
- Bakeable to 100 °C

DESCRIPTION

The Passivated Implanted Planar Silicon (PIPS) Detector is a product of modern semiconductor technology. In most applications, this detector replaces silicon surface barrier (SSB) detectors and diffused junction (DJ) detectors, both of which are still made the same way they were made in 1960. The PIPS detector has a number of advantages over SDB and DJ types:

- 1. All junction edges are buried no epoxy edge sealant is needed or used.
- $2. \ Contacts \ are \ ion-implanted \ to \ form \ precise, thin, abrupt junctions \ for \ good \ alpha \ resolution.$
- 3. Entrance window is stable and rugged it can be cleaned readily and reliably.
- 4. Leakage current is typically 1/8 to 1/100 of that of SSB and DJ detectors.
- 5. Dead layer (window) thickness is less than that of comparable SDB or DJ detectors.
- 6. Standard detectors are bakeable to 100 $^{\circ}\text{C}$ higher for special models.

The PIPS Detector is fabricated by the planar process using photolithographic techniques for defining device geometries. Proprietary techniques are used to provide precise control of the oxide passivation, and ion implantation is used to form the accurately controlled junctions necessary for low reverse leakage currents and thin entrance windows. The photolithographic technique lends itself to virtually any geometry which fits onto a diameter of 140 mm.

Resistivity of the uniform ion-implanted contacts can be controlled accurately to produce position-sensitive detectors with extremely thin entrance windows (<50 nm).

Low reverse current translates into low noise contribution. Shown by the newly introduced X-PIPS $^{\mathbb{N}}$ detector, an excellent room-temperature X-Ray detector.

Unlike SSB detectors which have raw junction edges that are epoxy sealed to achieve some measure of stability, the PIPS detector junctions are all buried within the silicon wafer. There are three major advantages to this innovation: 1) The device stability is not dependent upon an epoxy sealant; 2) There is little risk of microplasma breakdown which can afflict SSB detectors and 3) Leakage current is a small fraction of that of SSB or DJ detectors.



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The face contact (entrance window) of the PIPS detector is ion-implanted. Mirion has developed proprietary techniques for minimizing window thickness while retaining the ruggedness, reliability and stability inherent in this type of contact. The PIPS detector has a window that is substantially thinner than conventional SSBs and far thinner than any detector approaching it in ruggedness. A comparison is shown below:

Detector	Window Thickness (eq. Si)
PIPS	< 50 nm
SSB (Au Window)	≈ 80 nm
SSB (Al Window)	> 200 nm

This thin window not only improves typical resolution as normally measured but it exhibits an even greater improvement at close detector-source spacing which is necessary to achieve the high efficiency required for low-level alpha spectroscopy. The reason for this is very simple – at close detector-source spacing, peak broadening occurs because many alphas enter the detector at an acute angle – with a resultant variation in energy loss (or straggling) in the entrance window. With thinner windows, less straggling occurs.

Since the PIPS detector does not rely on delicate evaporated metallic contacts as do SSB detectors, but rather a passivated, implanted surface, it can be touched by hand and cleaned readily with a cotton ball dampened with isopropyl alcohol. This facility makes it possible to exploit applications heretofore reserved for diffused junction detectors which cannot compete with the PIPS in leakage current, resolution or window thickness.

Available in the Following Series					
Partially Depleted – Series PD Annular – Series AN					
Fully Depleted – Series FD	Custom Design – Series CD				
Alpha – Series A	X-PIPS Detector				
CAM – Series CAM	Single and Multi-element – Series SMEPS				

FULLY DEPLETED PLANAR PIPS DETECTORS: SERIES FD

The FD series of PIPS detectors are used in particle identification, detector telescopes and in other de/dx measurements. They are particularly good in thickness uniformity, 1 to 2 μ m for small active areas and 2 to 4 μ m for areas up to 900 mm². The FD series are normally supplied in a transmission mount with a radial microdot connector (model number suffix-RM). Resolution is conservatively specified with alpha particles entering through the rear contact which has an entrance window thickness of 1600 Å. The resolution through front contact, with a thickness of 500 Å is better. Typical operating voltages are 60 V for 300 μ m thick detectors and 100 V for 500 μ m thick detectors.

FULLY DEPLETED PIPS DETECTORS SERIES							
Thickness		30	0 microns		50	00 microns	
Active Area	Reso ke (FW	eV.	Model No.	ke	lution eV HM)	Model No.	
	α	β		α	β		
50	14	6	FD50-14-300RM*	14	6	FD50-15-500RM*	
150	15	8	FD150-15-300RM*	15	8	FD150-16-500RM*	
300	18	11	FD300-18-300RM*	17	10	FD300-17-500RM*	
450	18	12	FD450-18-300RM*	19	14	FD450-19-500RM*	
600	22	16	FD600-22-300RM	22	15	FD600-22-500RM	
900	24	17	FD900-24-300RM	24	17	FD900-24-500RM	

Resolution is given for 241 Am, 5.486 MeV alphas, using standard Mirion electronics and 0.5 μ s shaping time constant.

ALPHA PIPS DETECTORS: SERIES A

The A series of PIPS detectors is optimized for high-resolution, high sensitivity, and low-background *alpha spectroscopy*. The thin window of the PIPS detector provides enhanced resolution with the close detector-source spacing needed for high efficiency. The low leakage current helps minimize peak shift with temperature variation. Detectors in the A-PIPS series are fabricated with specially designed and selected packaging materials which reduce alpha background and are processed and tested in low-background conditions to avoid contamination from alpha-emitting radionuclides. Because of these measures, the background count rate for A-series PIPS detectors is typically less than 0.05 counts/hr/cm² in the energy range of 3 to 8 MeV. Alpha PIPS detectors have a minimum active thickness of greater than 140 µm which is sufficient for full absorption of alpha particles of up to 15 MeV. Typical operating voltages are 40 V or 60 V.

ALPHA PIPS DETECTORS							
Active Area mm²	Alpha Resolution keV	Typical Background (counts/day)	Model Number				
300	17	4	A300-17AM				
450	18	6	A450-18AM				
600	22	8	A600-22AM				
900	25	12	A900-25AM				
1200	32	16	A1200-32AM				

Resolution is given for $^{241}\text{Am},\,5.486$ MeV alphas, using standard Mirion electronics and 0.5 μs shaping time constant.

THICK PD PIPS DETECTORS							
Area (mm²)	Resol keV (F a		Thickness (μm)	Model No.			
150 300	14 16	9 11	1000 1000	PD150-14-1000AM PD300-16-1000AM			



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PARTIALLY DEPLETED PIPS DETECTORS: SERIES PD

The PD series of PIPS detectors finds widespread application in *charged particle spectroscopy*. With sizes ranging from 25 mm² to 5000 mm² and thicknesses from 100 to 1000 μ m, the PD series is adaptable to a wide variety of physics research and applied physics experiments. Partially-depleted PIPS detectors are normally supplied with our Axial microdot connector (model number suffix-AM) but can be ordered with other connectors at extra cost (see illustrations). Special packages and configurations are also available as are bare chips for use in customer-designed and fabricated systems. Typical operating voltages are 40 V for 100 μ m, 60 V for 300 μ m, 100 V for 500 μ m and 350 V for 1000 μ m thick detectors.

SERIES PD OPTIONS (CONSULT FACTORY)

Cryogenic (Prefix CY)

For operation at temperatures as low as -200 °C (77 °K).

Timing (Prefix TM)

Provides improved timing performance by the addition of 200 Å aluminum layer. For example a 450 mm² detector improves from 5 ns to 200 ps (FWHM). This is at the cost of \approx 4 keV (FWHM) in energy resolution. Available models marked with (†).

Bakeable (Prefix BK)

Packaged to endure bake temperatures up to 200 °C (non-operating).

PARTIALLY DEPLETED PIPS DETECTORS SERIES: PD									
Thickness	100 microns			300 microns			500 microns		
Active Area mm²		lution WHM) β	Model No.		lution WHM) β	Model No.		lution WHM) β	Model No.
25	12	6	PD25-12-100AM	11	5	PD25-11-300AM	10	4	PD25-10-500AM
50	12	6	PD50-12-100AM	11	5	PD50-11-300AM [†]	11	5	PD50-11-500AM [†]
150	14	9	PD150-14-100AM	13	8	PD150-13-300AM [†]	12	7	PD150-12-500AM [†]
300	16	11	PD300-16-100AM	15	10	PD300-15-300AM [†]	14	9	PD300-14-500AM [†]
450	17	12	PD450-17-100AM	16	11	PD450-16-300AM [†]	15	10	PD450-15-500AM [†]
600	22	17	PD600-22-100AM	20	15	PD600-20-300AM	20	15	PD600-20-500AM
900	27	22	PD900-27-100AM	22	19	PD900-22-300AM	22	17	PD900-22-500AM
1200	35	30	PD1200-35-100AM	25	20	PD1200-25-300AM	26	21	PD1200-26-500AM
2000				40	35	PD2000-40-300AM	35	30	PD2000-35-500AM
3000				55	50	PD3000-55-300AM	50	45	PD3000-50-500AM
5000				80	75	PD5000-80-300AM	75	70	PD5000-75-500AM

CAM PIPS DETECTORS: SERIES CAM

The Mirion CAM PIPS detector is a special version of the standard PIPS detector which has features that are very important in applications involving the measurement of alpha (and beta) particles from filters associated with continuous air monitors. The same device is ideal for measuring filter samples off-line. The CAM PIPS detector has aluminum and varnish coatings on the front surface. The aluminum coating allows the detector to be operated in ambient light and the varnish coating provides mechanical protection for the aluminum layer. The total entrance window thickness is less than 2 µm equivalent silicon. For convenience and cost savings the CAM PIPS detector is designed to operate with +15 to +24 V bias. This means that, for most systems, no H.V. bias supply is required. The detector operates from the dc voltage that is normally available to power the electronics in the system. For alphas, the detectors can operate with bias voltage as low as 15 V. With 70 V bias, the beta threshold (noise) is reduced to the levels indicated in the table and full depletion is achieved which ensures uniform response.

CAM PIPS DETECTORS								
Active Area (mm²)	Resolution (keV) Alpha Beta				Model Number			
300	36		15-24 V	45	CAM 300AM			
	33	15	70 V					
450	38		15-24 V	51	CAM 450AM			
	34	17	70 V					
490	39		15-24 V	54	CAM 490AM			
	35	18	70 V					
600	42		15-24 V	60	CAM 600AM			
	37	20	70 V					
900	45		15-24 V	66	CAM 900AM			
	39	22	70 V					
1200	55		15-24 V	75	CAM 1200AM			
	45	25	70 V					
1700	70		15-24 V	90	CAM 1700AM			
	55	30	70 V					
2000	80		15-24 V	110	CAM 2000AM			
	65	37	70 V					

Resolution is given for 241 Am, 5.486 MeV alphas, using standard Mirion electronics and 0.5 μ s shaping time constant.



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ANNULAR PIPS DETECTORS

These detectors have a 4 mm diameter through hole, and are available in RM mounts only. They are available in Partially Depleted (PD) and Fully Depleted (FD) versions which are 300 microns thick.

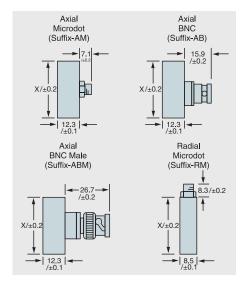
Active D	Diameter m)	Resoluti (FWI		Mount Size	Model Number
Inside	Outside	Alpha	Beta	mm ²	
5.5	19.5	20	15	300	ANFD300-20-300RM
5.5	19.5	18	14	300	ANPD300-18-300RM

^{**}Consult factory for availability.

MOUNTS AND DIMENSIONS

See chart and drawings. Detector face is recessed 1.0 mm in AM, AB, RM and ABM mounts.

Detector Size (mm²)	Active Diameter (mm)	Axial X (mm)	Radial X (mm)
25	5.7	16.7	19.4
50	8.0	16.7	19.4
100	11.3	23.6	26.1
150	13.8	23.6	26.1
200	16.0	28.6	31.6
300	19.5	28.6	31.6
450	23.9	32.0	34.8
490	25.0	33.4	N.A.
600	27.6	36.1	38.4
900	33.9	45.2	50.0
1200	39.1	48.8	53.0
1700	46.5	59.0	N.A.
2000	50.0	65.5	70.0
3000	61.8	76.2	80.0
5000	79.8	94.0	N.A.

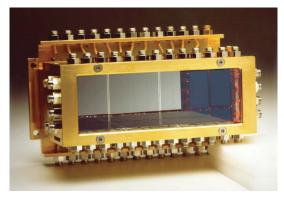


SINGLE AND MULTI-ELEMENT PIPS DETECTORS: SERIES SMEPS

As a result of Mirion's extensive work in Custom Design PIPS Detectors a number of these detectors, called SMEPS Detectors, are available at modest cost without a tooling charge. The Single Element PIPS Detectors are subdivided as one dimensional position sensitive detectors (resistive charge sharing over the implanted junction) and standard rectangular elements.

The Multi-element PIPS Detectors are subdivided into standard pad detectors, thin window pad detectors (<50 nm) and two dimensional position sensitive detectors. These detectors are generally mounted and wire bonded to an epoxy board for the ease of use.

Detailed information on these detectors can be found on the Mirion website under heading PIPS Detectors, Single and Multi-element PIPS Detectors.



This detector assembly manufactured by Mirion and others like it have been used in the discovery of super-heavy man-made elements at the Joint Institute for Nuclear Research in Dubna, Russia, at GSI Darmstadt in Germany, and at the Lawrence Berkeley National Laboratory in California.

CONNECTORS AVAILABLE

AM: Axial Microdot female

AB: Axial BNC female

ABM: Axial BNC male

- AM default for PD, CAM and A-SERIES AB, ABM, RM available as option
- · RM default for FD series



